FIG.1

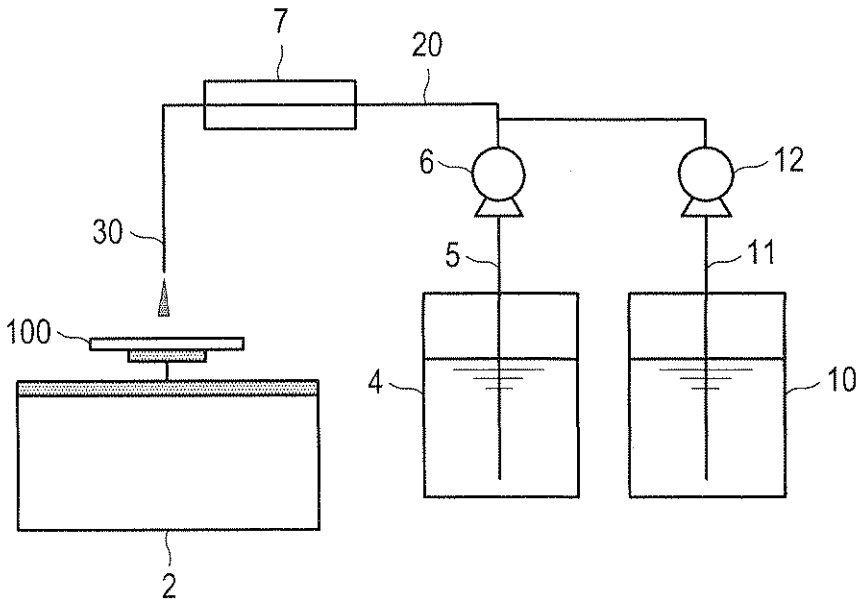


FIG.2

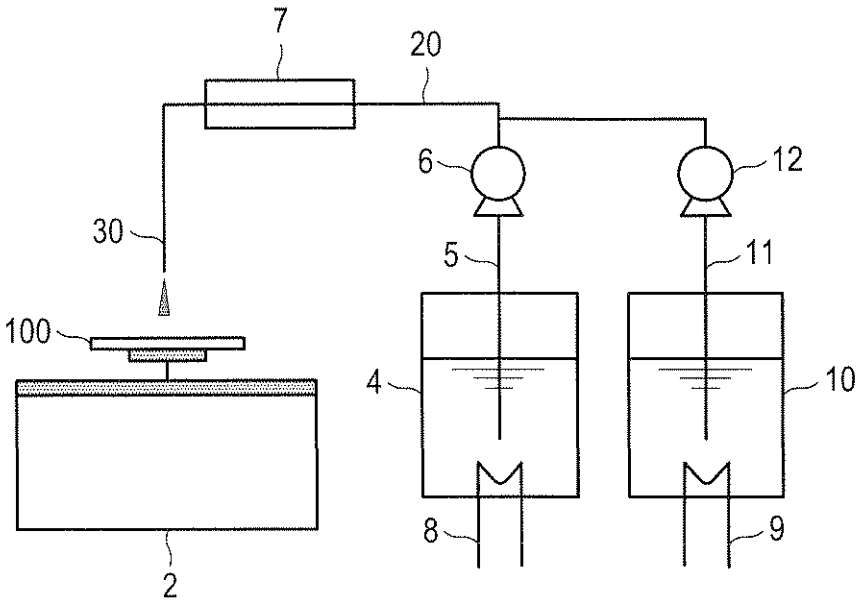


FIG.3

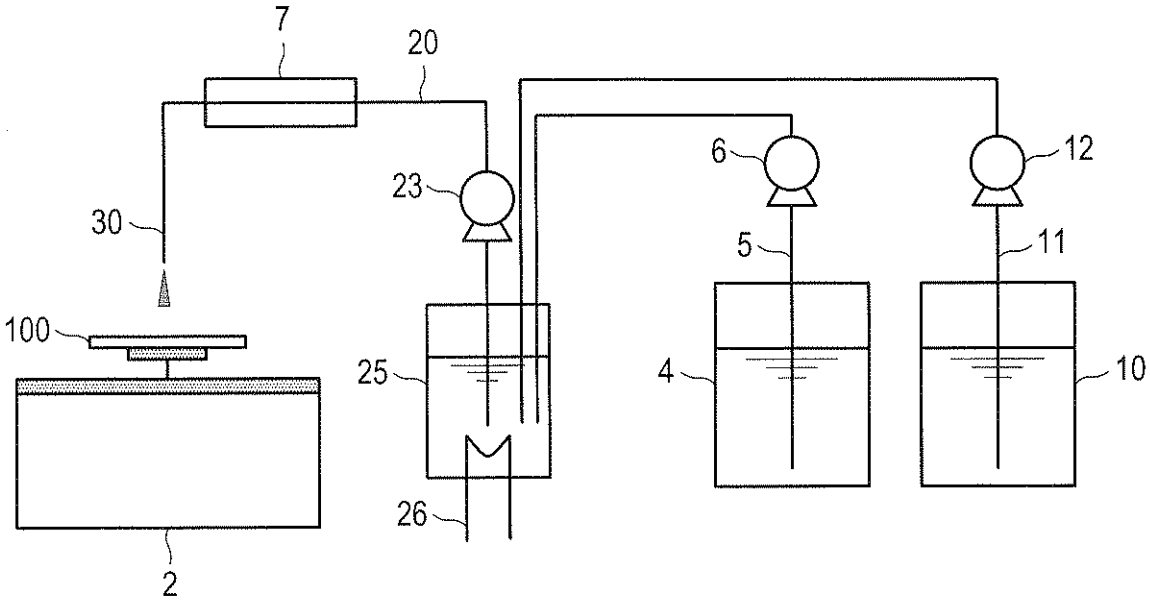


FIG.4

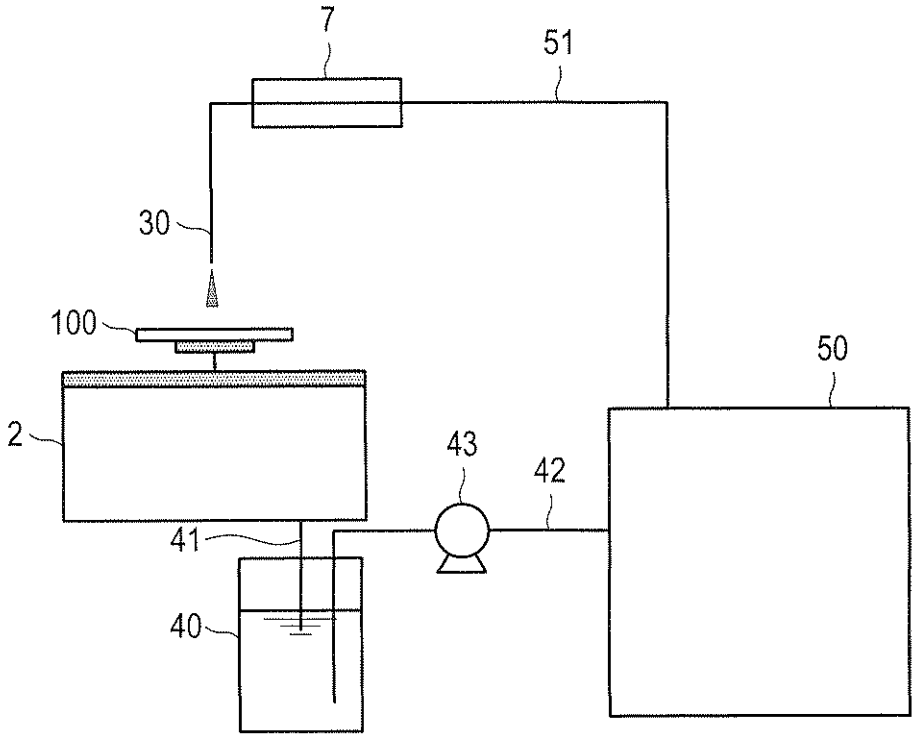


FIG.5

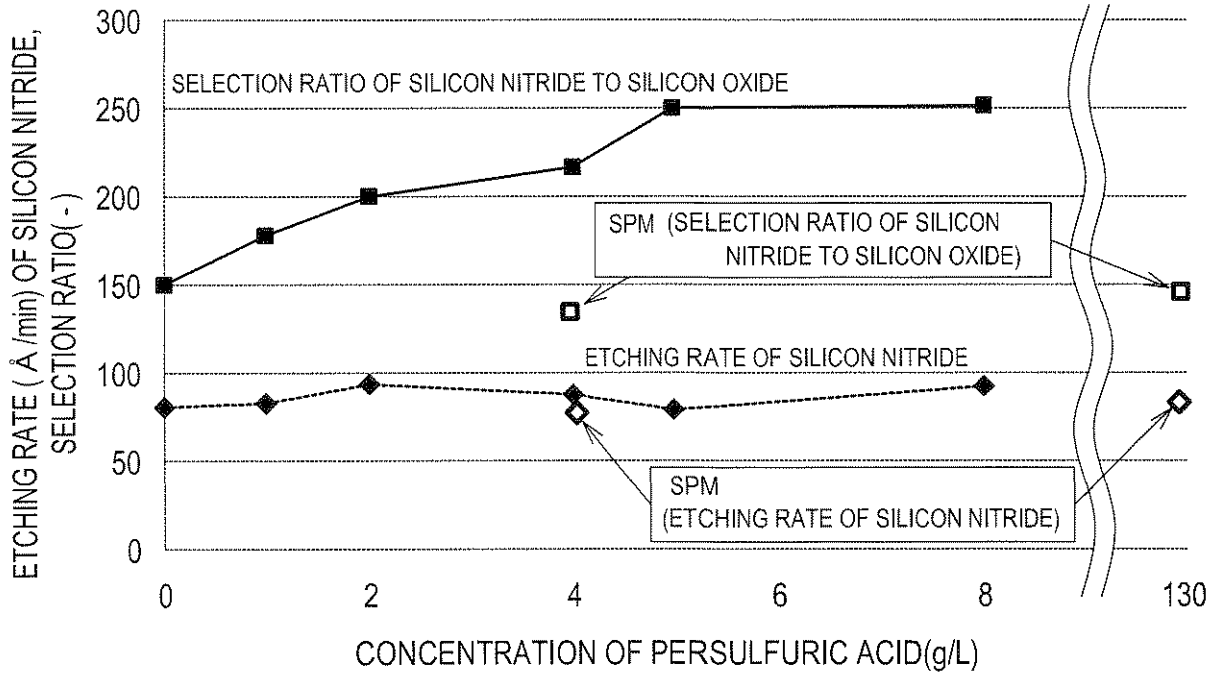
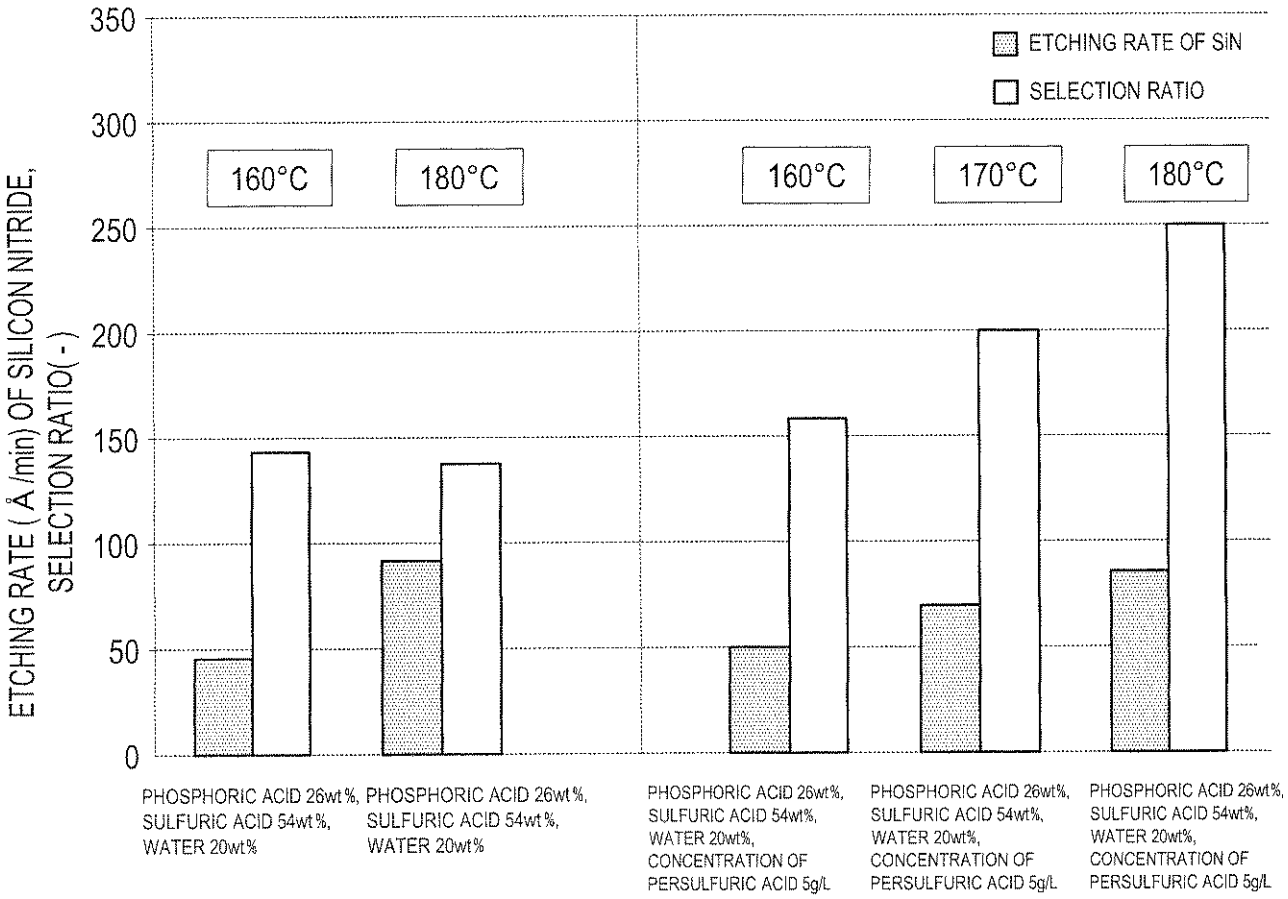

ETCHING RATE (Å /min) OF SILICON NITRIDE, SELECTION RATIO(-)
300
250
200
150
100
50
0
SELECTION RATIO OF SILICON NITRIDE TO SILICON OXIDE
SPM (SELECTION RATIO OF SILICON NITRIDE TO SILICON OXIDE)
ETCHING RATE OF SILICON NITRIDE
SPM (ETCHING RATE OF SILICON NITRIDE)
0
2
4
6
8
130
CONCENTRATION OF PERSULFURIC ACID(g/L)

FIG.6


ETCHING RATE (Å /min) OF SILICON NITRIDE, SELECTION RATIO(-)
350
300
250
200
150
100
50
0
ETCHING RATE OF SiN
SELECTION RATIO
160°C
180°C
160°C
170°C
180°C
PHOSPHORIC ACID 26wt%, SULFURIC ACID 54wt%, WATER 20wt%
PHOSPHORIC ACID 26wt%, SULFURIC ACID 54wt%, WATER 20wt%
PHOSPHORIC ACID 26wt%, SULFURIC ACID 54wt%, WATER 20wt%, CONCENTRATION OF PERSULFURIC ACID 5g/L
PHOSPHORIC ACID 26wt%, SULFURIC ACID 54wt%, WATER 20wt%, CONCENTRATION OF PERSULFURIC ACID 5g/L
PHOSPHORIC ACID 26wt%, SULFURIC ACID 54wt%, WATER 20wt%, CONCENTRATION OF PERSULFURIC ACID 5g/L